

# ANTREX Electronics

## Electronic Components Sourcing Information

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### Product Reference Information

|                      |                           |
|----------------------|---------------------------|
| <b>Part Number:</b>  | PSMN5R3-25MLD,115         |
| <b>Manufacturer:</b> | Nexperia USA Inc.         |
| <b>Package:</b>      | Please confirm with sales |
| <b>Availability:</b> | Please confirm with sales |

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**Note:**

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.



# PSMN5R3-25MLD

N-channel 25 V, 5.3 m $\Omega$  logic level MOSFET in LPAK33  
using NextPowerS3 Technology

6 April 2016

Product data sheet

## 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LPAK33 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

## 2. Features and benefits

- Ultra low  $Q_G$ ,  $Q_{GD}$  and  $Q_{OSS}$  for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1  $\mu$ A leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads for optimal visual solder inspection

## 3. Applications

- On-board DC:DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

## 4. Quick reference data

Table 1. Quick reference data

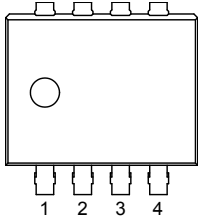
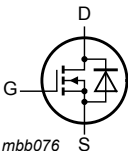
| Symbol    | Parameter               | Conditions                                                | Min | Typ | Max | Unit |
|-----------|-------------------------|-----------------------------------------------------------|-----|-----|-----|------|
| $V_{DS}$  | drain-source voltage    | 25 °C $\leq T_J \leq$ 175 °C                              | -   | -   | 25  | V    |
| $I_D$     | drain current           | $V_{GS} = 10$ V; $T_{mb} = 25$ °C; <a href="#">Fig. 2</a> | -   | -   | 70  | A    |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25$ °C; <a href="#">Fig. 1</a>                  | -   | -   | 51  | W    |

N-channel 25 V, 5.3 mΩ logic level MOSFET in LFAK33 using  
NextPowerS3 Technology

| Symbol                  | Parameter                        | Conditions                                                                                                                        |  | Min | Typ  | Max  | Unit |
|-------------------------|----------------------------------|-----------------------------------------------------------------------------------------------------------------------------------|--|-----|------|------|------|
| T <sub>j</sub>          | junction temperature             |                                                                                                                                   |  | -55 | -    | 175  | °C   |
| Static characteristics  |                                  |                                                                                                                                   |  |     |      |      |      |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C;<br><a href="#">Fig. 10</a>                                |  | -   | 7.07 | 8.49 | mΩ   |
|                         |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C;<br><a href="#">Fig. 10</a>                                 |  | -   | 5.25 | 5.9  | mΩ   |
| Dynamic characteristics |                                  |                                                                                                                                   |  |     |      |      |      |
| Q <sub>G(tot)</sub>     | total gate charge                | I <sub>D</sub> = 15 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 10 V;<br><a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>       |  | -   | 12.7 | -    | nC   |
|                         |                                  | I <sub>D</sub> = 15 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V;<br><a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>      |  | -   | 5.9  | -    | nC   |
|                         |                                  | I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V                                                               |  | -   | 6.6  | -    | nC   |
| Q <sub>GD</sub>         | gate-drain charge                | I <sub>D</sub> = 15 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V;<br><a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>      |  | -   | 1.3  | -    | nC   |
| Source-drain diode      |                                  |                                                                                                                                   |  |     |      |      |      |
| S                       | softness factor                  | I <sub>S</sub> = 15 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V;<br>V <sub>DS</sub> = 12 V; <a href="#">Fig. 16</a> |  | -   | 0.7  | -    |      |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                          | Graphic symbol                                                                                      |
|-----|--------|-----------------------------------|-------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------|
| 1   | S      | source                            |  <p>LFAK33 (SOT1210)</p> |  <p>mbb076</p> |
| 2   | S      | source                            |                                                                                                             |                                                                                                     |
| 3   | S      | source                            |                                                                                                             |                                                                                                     |
| 4   | G      | gate                              |                                                                                                             |                                                                                                     |
| mb  | D      | mounting base; connected to drain |                                                                                                             |                                                                                                     |

## 6. Ordering information

Table 3. Ordering information

| Type number   | Package |                                                                |         |
|---------------|---------|----------------------------------------------------------------|---------|
|               | Name    | Description                                                    | Version |
| PSMN5R3-25MLD | LFAK33  | Plastic single ended surface mounted package (LFAK33); 8 leads | SOT1210 |

## 7. Marking

Table 4. Marking codes

| Type number   | Marking code |
|---------------|--------------|
| PSMN5R3-25MLD | 5D325L       |

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                      | Parameter                                    | Conditions                                                                                                                                                                         |                     | Min | Max  | Unit |
|-----------------------------|----------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------|-----|------|------|
| $V_{DS}$                    | drain-source voltage                         | $25\text{ °C} \leq T_J \leq 175\text{ °C}$                                                                                                                                         |                     | -   | 25   | V    |
| $V_{DGR}$                   | drain-gate voltage                           | $25\text{ °C} \leq T_J \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$                                                                                                          |                     | -   | 25   | V    |
| $V_{GS}$                    | gate-source voltage                          |                                                                                                                                                                                    |                     | -20 | 20   | V    |
| $P_{tot}$                   | total power dissipation                      | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                                                                                                                   |                     | -   | 51   | W    |
| $I_D$                       | drain current                                | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                                                                                                          |                     | -   | 70   | A    |
|                             |                                              | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; <a href="#">Fig. 2</a>                                                                                                         |                     | -   | 50.3 | A    |
| $I_{DM}$                    | peak drain current                           | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 3</a>                                                                                        |                     | -   | 285  | A    |
| $T_{stg}$                   | storage temperature                          |                                                                                                                                                                                    |                     | -55 | 175  | °C   |
| $T_J$                       | junction temperature                         |                                                                                                                                                                                    |                     | -55 | 175  | °C   |
| $T_{sld(M)}$                | peak soldering temperature                   |                                                                                                                                                                                    |                     | -   | 260  | °C   |
| $V_{ESD}$                   | electrostatic discharge voltage              | HBM (JEDEC)                                                                                                                                                                        |                     | 300 | -    | V    |
| <b>Source-drain diode</b>   |                                              |                                                                                                                                                                                    |                     |     |      |      |
| $I_S$                       | source current                               | $T_{mb} = 25\text{ °C}$                                                                                                                                                            |                     | -   | 42.4 | A    |
| $I_{SM}$                    | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$                                                                                                                 |                     | -   | 285  | A    |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                                                    |                     |     |      |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $I_D = 15\text{ A}$ ; $V_{sup} \leq 25\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{J(init)} = 25\text{ °C}$ ; unclamped; $t_p = 315\text{ }\mu\text{s}$ | <a href="#">[1]</a> | -   | 76.7 | mJ   |

[1] Protected by 100% test

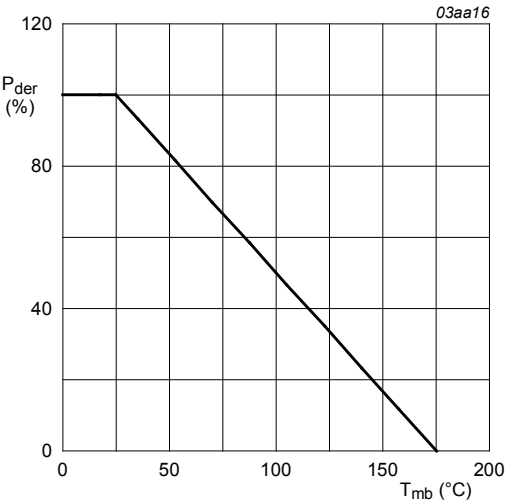
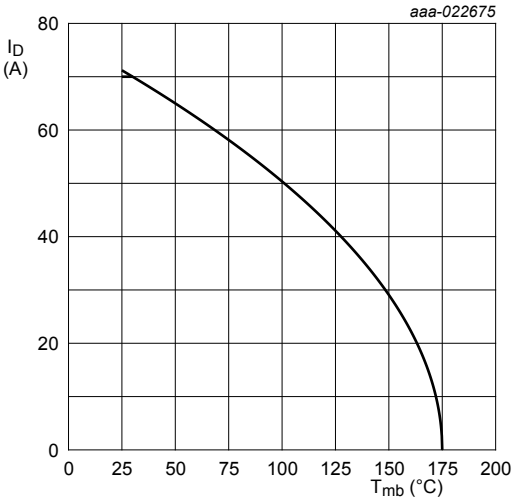


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

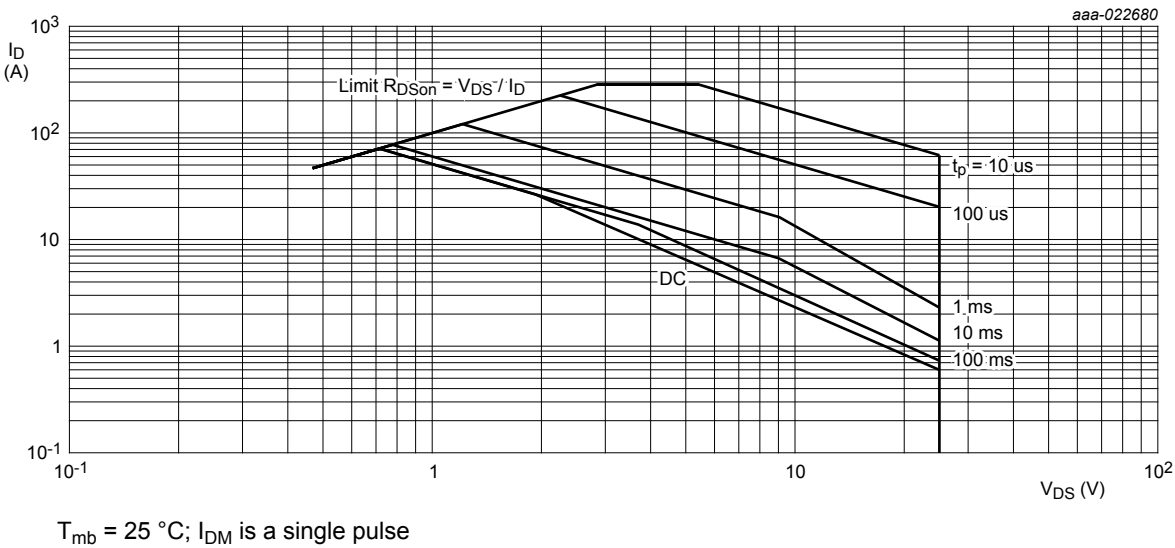
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



$V_{GS} \geq 10$  V  
(1) Capped at 70A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 71A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \geq 25^{\circ}C$$



$T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions | Min | Typ  | Max  | Unit |
|----------------|---------------------------------------------------|------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 4     | -   | 2.55 | 2.95 | K/W  |

| Symbol        | Parameter                                         | Conditions             |  | Min | Typ | Max | Unit |
|---------------|---------------------------------------------------|------------------------|--|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance<br>from junction to<br>ambient | <a href="#">Fig. 5</a> |  | -   | 57  | -   | K/W  |
|               |                                                   | <a href="#">Fig. 6</a> |  | -   | 178 | -   | K/W  |

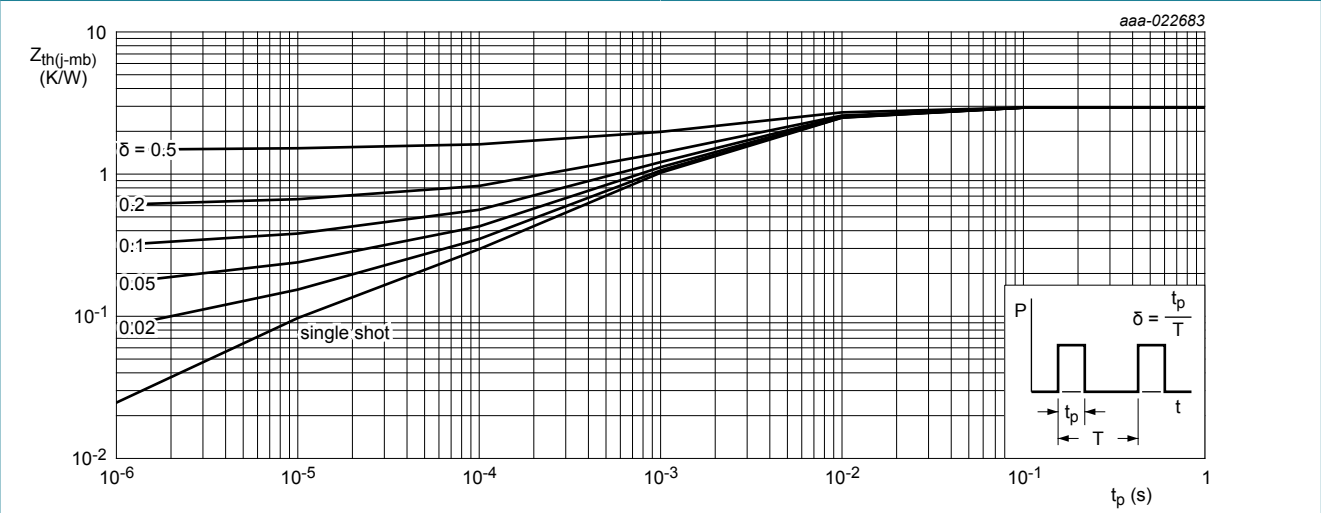


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

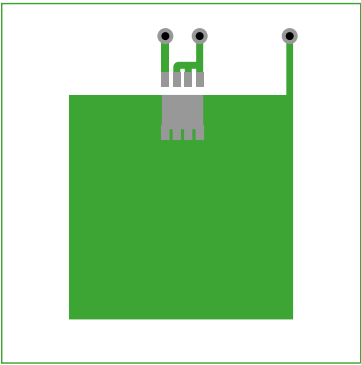


Fig. 5. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper

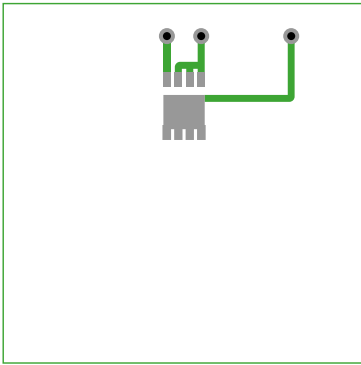


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

10. Characteristics

Table 7. Characteristics

| Symbol                 | Parameter                         | Conditions                                             |  | Min  | Typ | Max | Unit |
|------------------------|-----------------------------------|--------------------------------------------------------|--|------|-----|-----|------|
| Static characteristics |                                   |                                                        |  |      |     |     |      |
| $V_{(BR)DSS}$          | drain-source<br>breakdown voltage | $I_D = 250\ \mu A; V_{GS} = 0\ V; T_J = 25\ ^\circ C$  |  | 25   | -   | -   | V    |
|                        |                                   | $I_D = 250\ \mu A; V_{GS} = 0\ V; T_J = -55\ ^\circ C$ |  | 22.5 | -   | -   | V    |
| $V_{GS(th)}$           | gate-source threshold<br>voltage  | $I_D = 1\ mA; V_{DS}=V_{GS}; T_J = 25\ ^\circ C$       |  | 1.2  | 1.8 | 2.2 | V    |

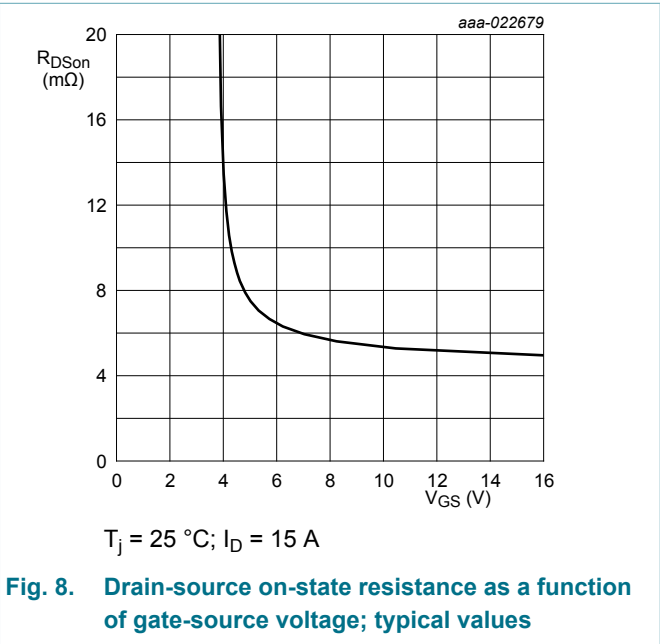
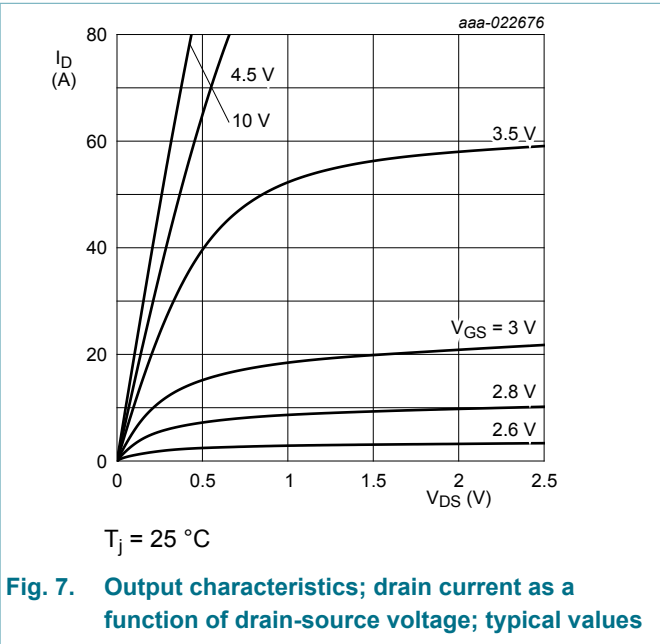
N-channel 25 V, 5.3 mΩ logic level MOSFET in LPAK33 using  
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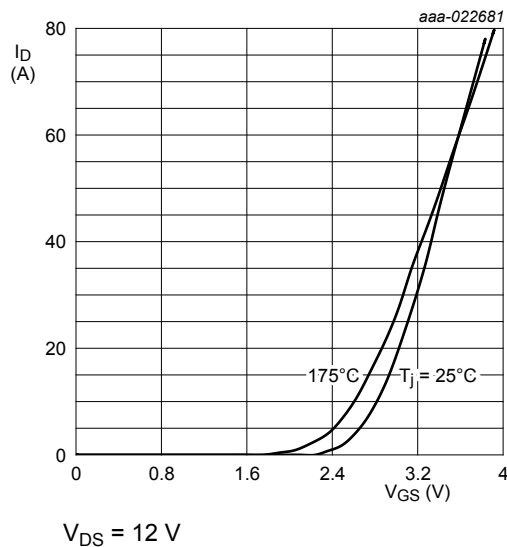
| Symbol                         | Parameter                                                | Conditions                                                                                                                    | Min | Typ  | Max   | Unit          |
|--------------------------------|----------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------|-----|------|-------|---------------|
| $\Delta V_{GS(th)}/\Delta T$   | gate-source threshold voltage variation with temperature | $25\text{ }^{\circ}\text{C} \leq T_j \leq 175\text{ }^{\circ}\text{C}$                                                        | -   | -4.3 | -     | mV/K          |
| $I_{DSS}$                      | drain leakage current                                    | $V_{DS} = 20\text{ V}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$                                                 | -   | -    | 1     | $\mu\text{A}$ |
|                                |                                                          | $V_{DS} = 20\text{ V}; V_{GS} = 0\text{ V}; T_j = 125\text{ }^{\circ}\text{C}$                                                | -   | 1.51 | -     | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current                                     | $V_{GS} = 20\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$                                                 | -   | -    | 100   | nA            |
|                                |                                                          | $V_{GS} = -20\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$                                                | -   | -    | 100   | nA            |
| $R_{DS(on)}$                   | drain-source on-state resistance                         | $V_{GS} = 4.5\text{ V}; I_D = 15\text{ A}; T_j = 25\text{ }^{\circ}\text{C};$<br><a href="#">Fig. 10</a>                      | -   | 7.07 | 8.49  | mΩ            |
|                                |                                                          | $V_{GS} = 4.5\text{ V}; I_D = 15\text{ A}; T_j = 175\text{ }^{\circ}\text{C};$<br><a href="#">Fig. 10; Fig. 11</a>            | -   | -    | 14.43 | mΩ            |
|                                |                                                          | $V_{GS} = 10\text{ V}; I_D = 15\text{ A}; T_j = 25\text{ }^{\circ}\text{C};$<br><a href="#">Fig. 10</a>                       | -   | 5.25 | 5.9   | mΩ            |
|                                |                                                          | $V_{GS} = 10\text{ V}; I_D = 15\text{ A}; T_j = 175\text{ }^{\circ}\text{C};$<br><a href="#">Fig. 10; Fig. 11</a>             | -   | -    | 10.03 | mΩ            |
| $R_G$                          | gate resistance                                          | $f = 1\text{ MHz}$                                                                                                            | -   | 0.75 | -     | Ω             |
| <b>Dynamic characteristics</b> |                                                          |                                                                                                                               |     |      |       |               |
| $Q_{G(tot)}$                   | total gate charge                                        | $I_D = 15\text{ A}; V_{DS} = 12\text{ V}; V_{GS} = 10\text{ V};$<br><a href="#">Fig. 12; Fig. 13</a>                          | -   | 12.7 | -     | nC            |
|                                |                                                          | $I_D = 15\text{ A}; V_{DS} = 12\text{ V}; V_{GS} = 4.5\text{ V};$<br><a href="#">Fig. 12; Fig. 13</a>                         | -   | 5.9  | -     | nC            |
|                                |                                                          | $I_D = 0\text{ A}; V_{DS} = 0\text{ V}; V_{GS} = 10\text{ V}$                                                                 | -   | 6.6  | -     | nC            |
| $Q_{GS}$                       | gate-source charge                                       | $I_D = 15\text{ A}; V_{DS} = 12\text{ V}; V_{GS} = 4.5\text{ V};$<br><a href="#">Fig. 12; Fig. 13</a>                         | -   | 2.7  | -     | nC            |
| $Q_{GS(th)}$                   | pre-threshold gate-source charge                         |                                                                                                                               | -   | 1.5  | -     | nC            |
| $Q_{GS(th-pl)}$                | post-threshold gate-source charge                        |                                                                                                                               | -   | 1.2  | -     | nC            |
| $Q_{GD}$                       | gate-drain charge                                        |                                                                                                                               | -   | 1.3  | -     | nC            |
| $V_{GS(pl)}$                   | gate-source plateau voltage                              | $I_D = 15\text{ A}; V_{DS} = 12\text{ V};$ <a href="#">Fig. 12; Fig. 13</a>                                                   | -   | 3    | -     | V             |
| $C_{iss}$                      | input capacitance                                        | $V_{DS} = 12\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$<br>$T_j = 25\text{ }^{\circ}\text{C};$ <a href="#">Fig. 14</a> | -   | 858  | -     | pF            |
| $C_{oss}$                      | output capacitance                                       |                                                                                                                               | -   | 628  | -     | pF            |
| $C_{rss}$                      | reverse transfer capacitance                             |                                                                                                                               | -   | 55   | -     | pF            |
| $t_{d(on)}$                    | turn-on delay time                                       | $V_{DS} = 12\text{ V}; R_L = 1\text{ }^{\circ}\Omega; V_{GS} = 4.5\text{ V};$<br>$R_{G(ext)} = 5\text{ }^{\circ}\Omega$       | -   | 8.4  | -     | ns            |
| $t_r$                          | rise time                                                |                                                                                                                               | -   | 8    | -     | ns            |
| $t_{d(off)}$                   | turn-off delay time                                      |                                                                                                                               | -   | 9    | -     | ns            |
| $t_f$                          | fall time                                                |                                                                                                                               | -   | 4.9  | -     | ns            |

N-channel 25 V, 5.3 mΩ logic level MOSFET in LPAK33 using NextPowerS3 Technology

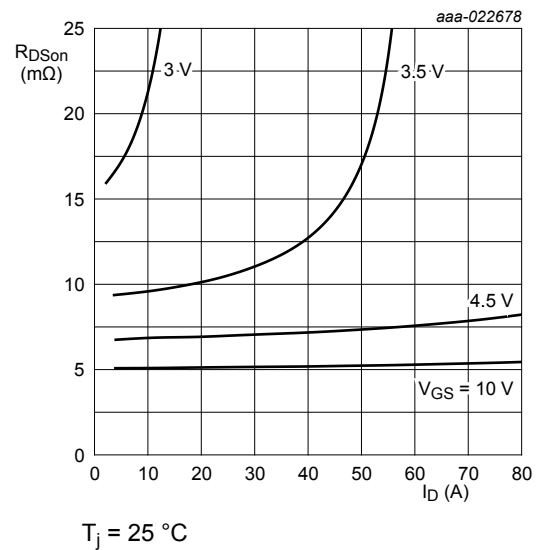
| Symbol             | Parameter                  | Conditions                                                                                                                             |                     | Min | Typ  | Max | Unit |
|--------------------|----------------------------|----------------------------------------------------------------------------------------------------------------------------------------|---------------------|-----|------|-----|------|
| $Q_{oss}$          | output charge              | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 12\text{ V}$ ; $f = 1\text{ MHz}$ ; $T_j = 25\text{ °C}$                                             |                     | -   | 10.1 | -   | nC   |
| Source-drain diode |                            |                                                                                                                                        |                     |     |      |     |      |
| $V_{SD}$           | source-drain voltage       | $I_S = 10\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 15</a>                                           |                     | -   | 0.82 | 1.2 | V    |
| $t_{rr}$           | reverse recovery time      | $I_S = 15\text{ A}$ ; $dI_S/dt = -100\text{ A/}\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 12\text{ V}$ ; <a href="#">Fig. 16</a> |                     | -   | 19.3 | -   | ns   |
| $Q_r$              | recovered charge           |                                                                                                                                        | <a href="#">[1]</a> | -   | 10.8 | -   | nC   |
| $t_a$              | reverse recovery rise time |                                                                                                                                        |                     | -   | 11.2 | -   | ns   |
| $t_b$              | reverse recovery fall time |                                                                                                                                        |                     | -   | 8    | -   | ns   |
| S                  | softness factor            |                                                                                                                                        |                     | -   | 0.7  | -   |      |

[1] includes capacitive recovery

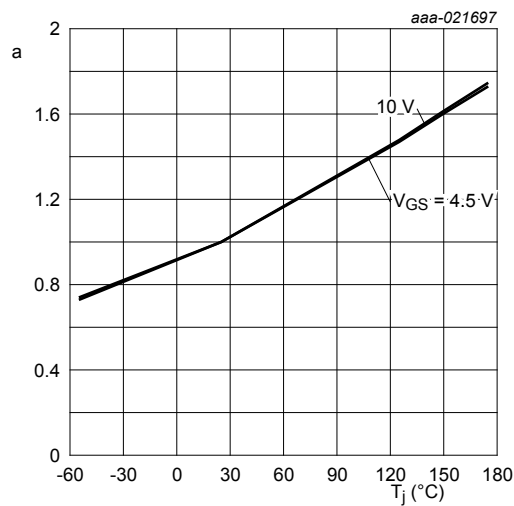




**Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**

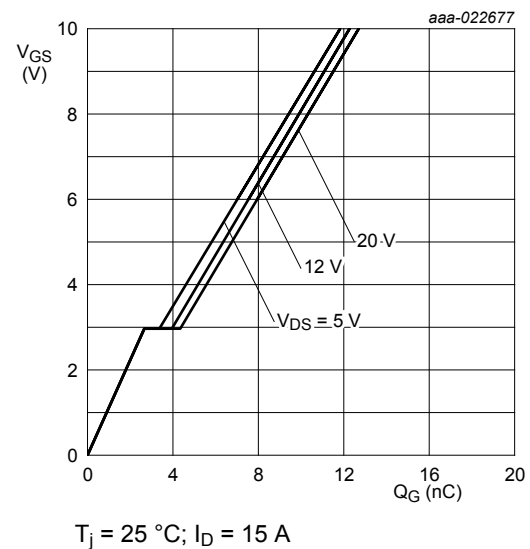


**Fig. 10. Drain-source on-state resistance as a function of drain current; typical values**



**Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$



**Fig. 12. Gate-source voltage as a function of gate charge; typical values**

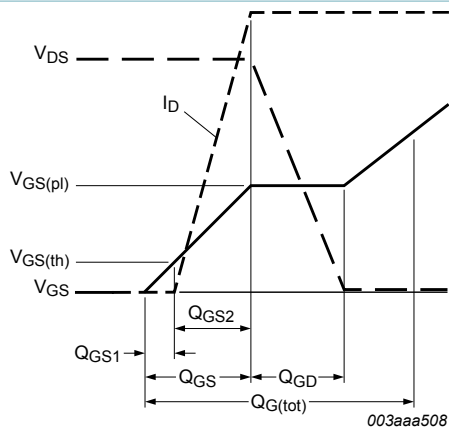
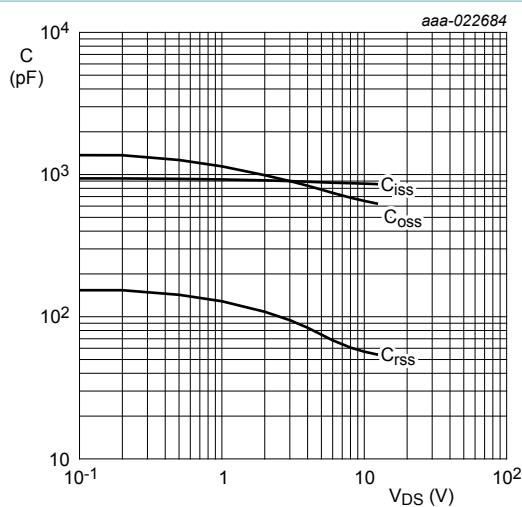
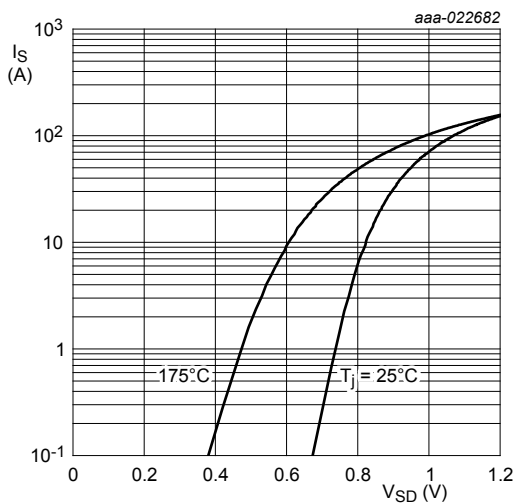


Fig. 13. Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$ ;  $f = 1 \text{ MHz}$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0 \text{ V}$

Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

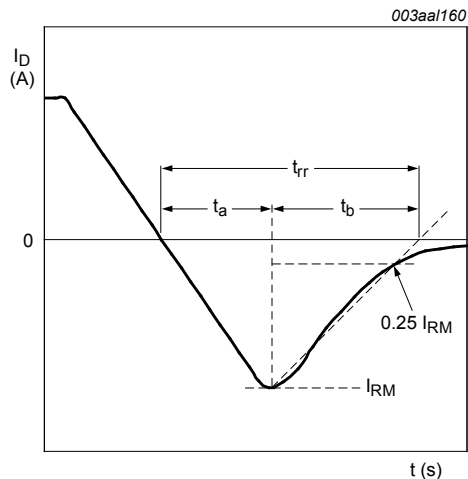


Fig. 16. Reverse recovery timing definition

11. Package outline

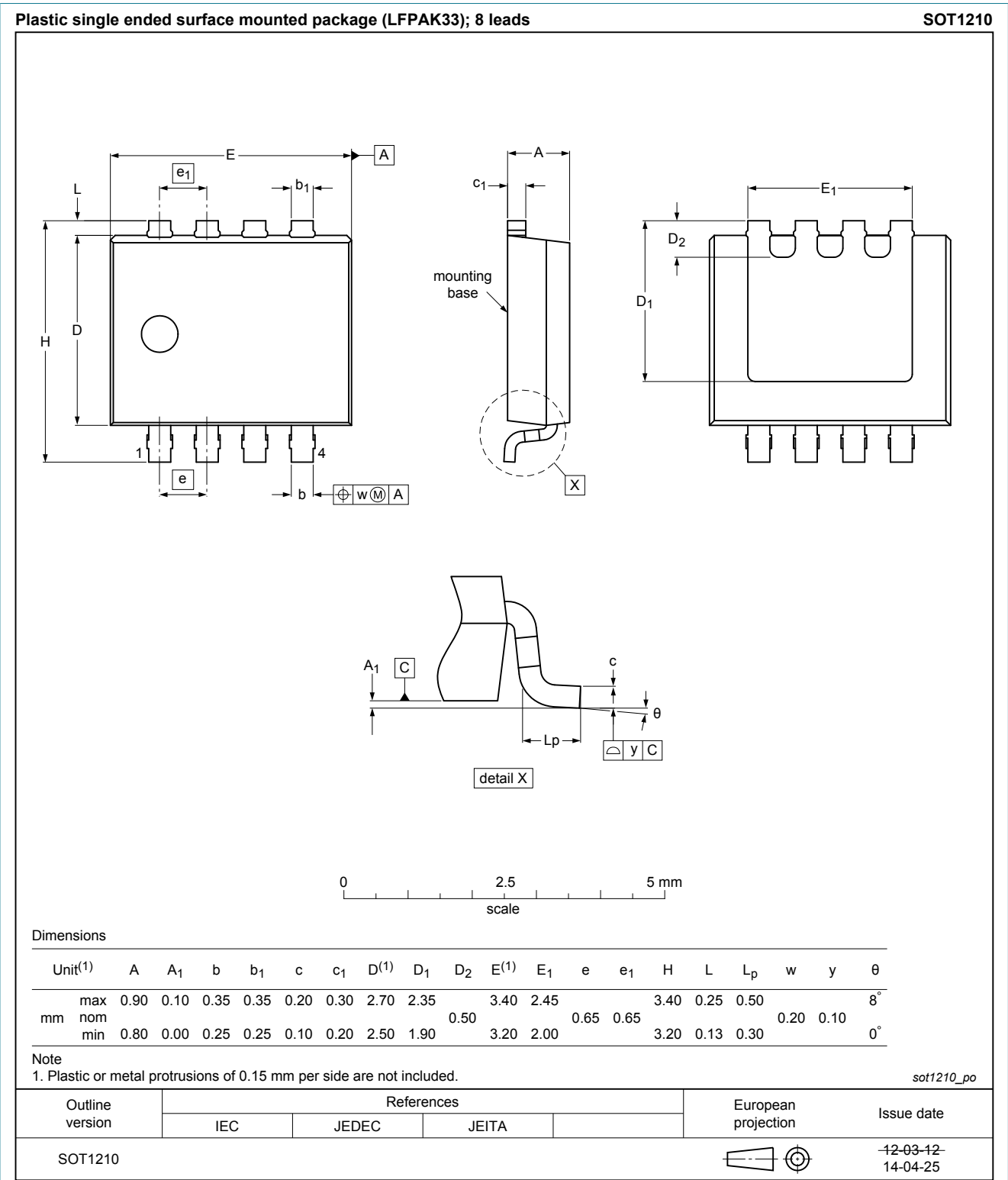


Fig. 17. Package outline LPAK33 (SOT1210)

## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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N-channel 25 V, 5.3 mΩ logic level MOSFET in LFPK33 using  
NextPowerS3 Technology

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